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S/N 08/902,809

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Klaus Florian Schuegraf et al.

Examiner: O Nadav

Serial No.: 08/902,809

Group Art Unit: 2811

Filed: July 30, 1997

Docket: 303.278US1

Title: SELECTIVE SPACER TO PREVENT METAL OXIDE FORMATION
DURING POLYCIDE REOXIDATION



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TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents
Washington, D.C. 20231

In response to the Office Action dated January 11, 1999, Applicants respectfully request that the Examiner consider and enter the following amendments and remarks in connection with the above-identified patent application.

IN THE CLAIMS

Please cancel claims 32-35.

Please amend the claims as follows:

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23. (Amended) A semiconductor device comprising:
an oxide [active area] layer;
at least one feature over the oxide [active area] layer, the feature having a surface and being contiguous with the oxide [active area] layer at a boundary; and
a spacer comprising silicon nitride or an amorphous silicon film covering the surface of the feature and terminating at the boundary wherein the spacer is not in contact with the oxide [active area] layer.

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24. (Amended) The semiconductor device of claim 23 wherein:

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;
[the spacer comprises silicon nitride or an amorphous silicon film;] and
the surface of the feature comprises sidewalls of the electrode.

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